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(71) Applicant: TOSHIBA CORP

(72) Inventor: YOSHINO CHIHIRO

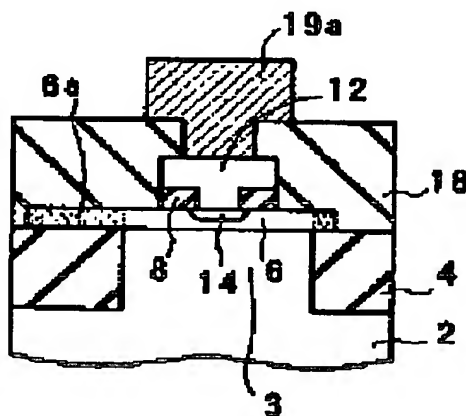
(74) Representative:

(54) SEMICONDUCTOR DEVICE AND PRODUCING METHOD THEREFOR

(57) Abstract:

PROBLEM TO BE SOLVED: To achieve acceleration in speed and reduction of power consumption as much as possible, even if microminiaturized and to prevent the change of a current gain caused by emitter width as much as possible.

SOLUTION: This device is provided with a first conductive base layer 6 formed on a device region 3 of a semiconductor substrate, second conductive emitter region 14 formed on the surface region of this base layer 6, insulating film 8 formed on the base layer 6 and composed of a single layer having an emitter opening on the emitter region 14, and an emitter electrode 12 formed on the insulating film so as to embed the emitter opening.



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